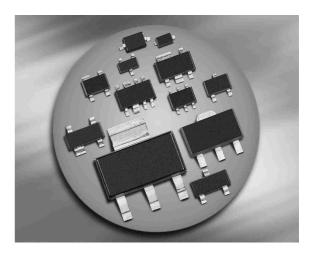


Silicon Variable Capacitance Diode

- For VHF tuned circuit applications
- High figure of merit
- Pb-free (RoHS compliant) package





BB439



Туре	Package	Configuration	L _S (nH)	Marking
BB439	SOD323	single	1.8	white 2

Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Diode reverse voltage	V _R	28	V	
Peak reverse voltage	V _{RM}	30		
($R \ge 5 \mathrm{k} \Omega$)				
Forward current	I _F	20	mA	
Operating temperature range	T _{op}	-55 125	°C	
Storage temperature	T _{stg}	-55 150		



Parameter	Symbol		Values		
		min.	typ.	max.	1
DC Characteristics					
Reverse current	I _R				nA
V _R = 28 V		-	-	20	
<i>V</i> _R = 28 V, <i>T</i> _A = 85 °C		-	-	200	
AC Characteristics					
Diode capacitance	CT				pF
V _R = 1 V, <i>f</i> = 1 MHz		-	43	-	
<i>V</i> _R = 2 V, <i>f</i> = 1 MHz		31.5	34.5	37.5	
<i>V</i> _R = 3 V, <i>f</i> = 1 MHz		26.5	29	31.5	
V _R = 25 V, <i>f</i> = 1 MHz		4.3	5.1	6	
Capacitance ratio	C _{T2} /C _{T25}	6	6.9	8]
$V_{\rm R}$ = 2 V, $V_{\rm R}$ = 25 V, f = 1 MHz					
Capacitance ratio	C _{T3} /C _{T25}	5	5.8	6.5	
$V_{\rm R}$ = 3 V, $V_{\rm R}$ = 25 V, f = 1 MHz					
Capacitance matching ¹⁾	$\Delta C_{T}/C_{T}$	-	-	3	%
$V_{\rm R}$ = 3 V, $V_{\rm R}$ = 25 V, f = 1 MHz					
Series resistance	r _S	-	0.35	0.5	Ω
V _R = 10 V, <i>f</i> = 100 MHz					
Figure of merit	Q				
V _R = 3 V, <i>f</i> = 50 MHz		-	280	-	
<i>V</i> _R = 25 V, <i>f</i> = 200 MHz		-	600	-	

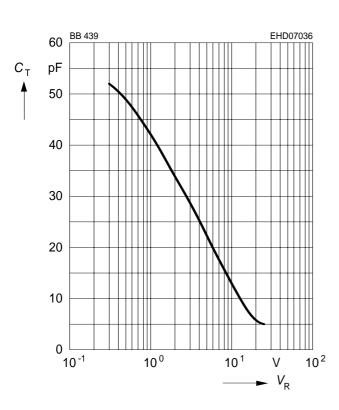
Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

¹For details please refer to Application Note 047.



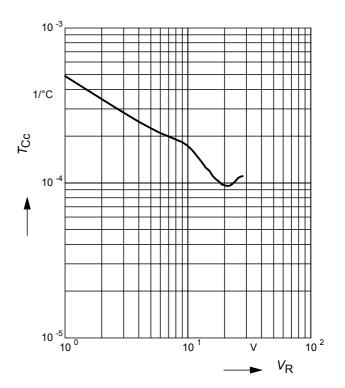
Diode capacitance $C_{T} = f(V_{R})$

f = 1 MHz

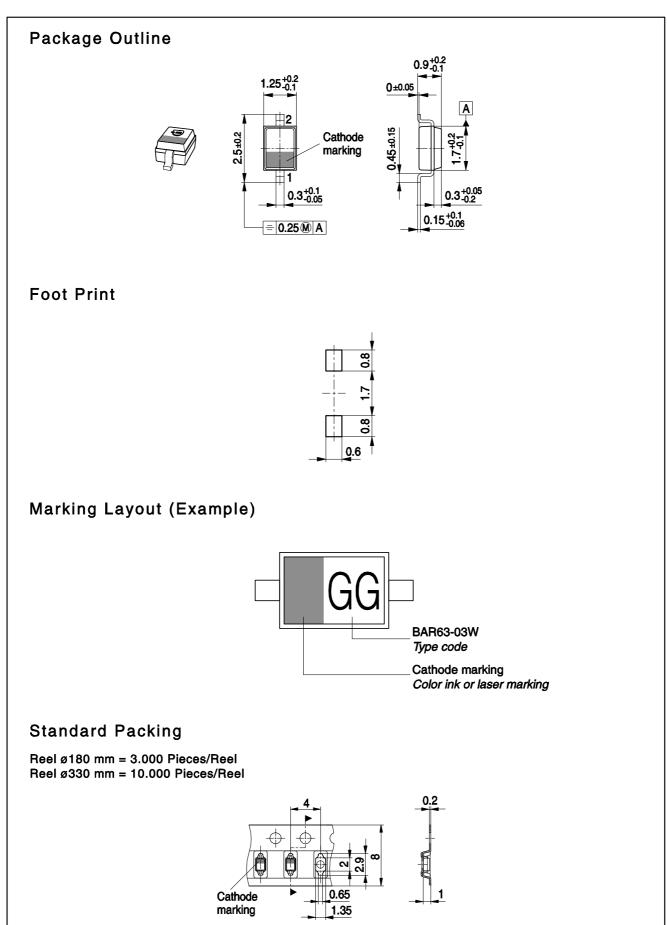


Temperature coefficient of the diode

capacitance $T_{Cc} = f(V_R)$









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